

# MOSFET

Metal Oxide Semiconductor Field Effect Transistor

## CoolMOS C6

650V CoolMOS™ C6 Power Transistor  
IPW65R070C6

## Data Sheet

Rev. 2.0, 2011-03-15  
Final

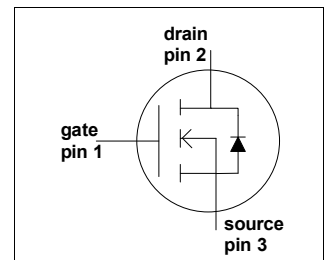
Industrial & Multimarket

## 650V CoolMOS™ C6 Power Transistor

IPW65R070C6

### 1 Description

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ C6 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The offered devices provide all benefits of a fast switching SJ MOSFET while not sacrificing ease of use. Extremely low switching and conduction losses make switching applications even more efficient, more compact, lighter, and cooler.



#### Features

- Extremely low losses due to very low FOM  $R_{DS(on)} \cdot Q_g$  and  $E_{oss}$
- Very high commutation ruggedness
- Easy to use/drive
- Qualified for industrial grade applications according to JEDEC<sup>1)</sup>
- Pb-free plating, Halogen free mold compound

#### Applications

PFC stages, hard switching PWM stages and resonant switching PWM stages for e.g. PC Silverbox, LCD & PDP TV, Lighting, Server, Telecom, UPS and Solar.

*Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.*



**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	700	V
$R_{DS(on),max}$	0.07	$\Omega$
$Q_{g,typ}$	170	nC
$I_{D,pulse}$	150	A
$E_{oss} @ 400V$	13	$\mu J$
Body diode $di/dt$	300	A/ $\mu s$

#### Related Links

- [IFX CoolMOS Webpage](#)
- [IFX Design tools](#)

Type	Package	Marking
IPW65R070C6	PG-TO247	65C6070

1) J-STD20 and JESD22

## Table of Contents

1	Description .....	2
	Table of Contents .....	3
2	Maximum ratings .....	4
3	Thermal characteristics .....	4
4	Electrical characteristics .....	5
5	Electrical characteristics diagrams .....	7
6	Package outlines .....	11
7	Revision History .....	12

## 2 Maximum ratings

at  $T_j = 25\text{ °C}$ , unless otherwise specified.

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current <sup>1)</sup>	$I_D$	-	-	53.5	A	$T_C = 25\text{ °C}$
				33.8		$T_C = 100\text{ °C}$
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	-	-	150	A	$T_C = 25\text{ °C}$
Avalanche energy, single pulse	$E_{AS}$	-	-	1160	mJ	$I_D = 9.3\text{ A}, V_{DD} = 50\text{ V}$
Avalanche energy, repetitive	$E_{AR}$	-	-	1.76		$I_D = 9.3\text{ A}, V_{DD} = 50\text{ V}$
Avalanche current, repetitive	$I_{AR}$	-	-	9.3	A	
MOSFET dv/dt ruggedness	dv/dt	-	-	50	V/ns	$V_{DS} = 0 \dots 480\text{ V}$
Gate source voltage	$V_{GS}$	-20	-	20	V	static
		-30		30		AC ( $f > 1\text{ Hz}$ )
Power dissipation	$P_{tot}$	-	-	391	W	$T_C = 25\text{ °C}$
Operating and storage temperature	$T_j, T_{stg}$	-55	-	150	°C	
Mounting torque		-	-	60	Ncm	M3 and M3.5 screws
Continuous diode forward current	$I_S$	-	-	46.3	A	$T_C = 25\text{ °C}$
Diode pulse current <sup>2)</sup>	$I_{S,pulse}$	-	-	150	A	$T_C = 25\text{ °C}$
Reverse diode dv/dt <sup>3)</sup>	dv/dt	-	-	15	V/ns	$V_{DS} = 0 \dots 400\text{ V}, I_{SD} \leq I_D, T_j = 25\text{ °C}$
Maximum diode commutation speed <sup>3)</sup>	di/dt	-	-	300	A/ $\mu$ s	

1) Limited by  $T_{j,max}$ . Maximum duty cycle  $D = 0.75$

2) Pulse width  $t_p$  limited by  $T_{j,max}$

3) Identical low side and high side switch with identical  $R_G$ ;  $V_{peak} < V_{(BR)DSS}$ ;  $T_j < T_{j,max}$

## 3 Thermal characteristics

**Table 3 Thermal characteristics TO-247**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	-	0.32	°C/W	
Thermal resistance, junction - ambient	$R_{thJA}$	-	-	62		leaded
Soldering temperature, wavesoldering only allowed at leads	$T_{sold}$	-	-	260	°C	1.6 mm (0.063 in.) from case for 10 s

## 4 Electrical characteristics

Electrical characteristics, at  $T_J=25\text{ °C}$ , unless otherwise specified.

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	650	-	-	V	$V_{GS}=0\text{ V}$ , $I_D=1.0\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.5	3	3.5		$V_{DS}=V_{GS}$ , $I_D=1.76\text{ mA}$
Zero gate voltage drain current	$I_{DSS}$	-	-	1	$\mu\text{A}$	$V_{DS}=650\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_J=25\text{ °C}$
		-	50	-		$V_{DS}=650\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_J=150\text{ °C}$
Gate-source leakage current	$I_{GSS}$	-	-	100	nA	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.063	0.07	$\Omega$	$V_{GS}=10\text{ V}$ , $I_D=17.6\text{ A}$ , $T_J=25\text{ °C}$
		-	0.164	-		$V_{GS}=10\text{ V}$ , $I_D=17.6\text{ A}$ , $T_J=150\text{ °C}$
Gate resistance	$R_G$	-	0.85	-	$\Omega$	$f=1\text{ MHz}$ , open drain

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition	
		Min.	Typ.	Max.			
Input capacitance	$C_{iss}$	-	3900	-	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=100\text{ V}$ , $f=1\text{ MHz}$	
Output capacitance	$C_{oss}$	-	215	-			
Effective output capacitance, energy related <sup>1)</sup>	$C_{o(er)}$	-	140	-			$V_{GS}=0\text{ V}$ , $V_{DS}=0\dots480\text{ V}$
Effective output capacitance, time related <sup>2)</sup>	$C_{o(tr)}$	-	670	-			$I_D=\text{constant}$ , $V_{GS}=0\text{ V}$ $V_{DS}=0\dots480\text{ V}$
Turn-on delay time	$t_{d(on)}$	-	17	-	ns	$V_{DD}=400\text{ V}$ , $V_{GS}=13\text{ V}$ , $I_D=26.3\text{ A}$ , $R_G=1.8\text{ }\Omega$	
Rise time	$t_r$	-	17	-			
Turn-off delay time	$t_{d(off)}$	-	90	-			
Fall time	$t_f$	-	6	-			

1)  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{(BR)DSS}$

2)  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{(BR)DSS}$

**Table 6 Gate charge characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{gs}$	-	20	-	nC	$V_{DD}=480\text{ V}$ , $I_D=26.3\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	$Q_{gd}$	-	85	-		
Gate charge total	$Q_g$	-	170	-		
Gate plateau voltage	$V_{plateau}$	-	5.5	-	V	

**Table 7 Reverse diode characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	$V_{SD}$	-	0.9	-	V	$V_{GS}=0\text{ V}$ , $I_F=26.3\text{ A}$ , $T_j=25\text{ °C}$
Reverse recovery time	$t_{rr}$	-	730	-	ns	$V_R=400\text{ V}$ , $I_F=26.3\text{ A}$ , $di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	$Q_{rr}$	-	19	-	$\mu\text{C}$	
Peak reverse recovery current	$I_{rrm}$	-	50	-	A	

5 Electrical characteristics diagrams

Table 8

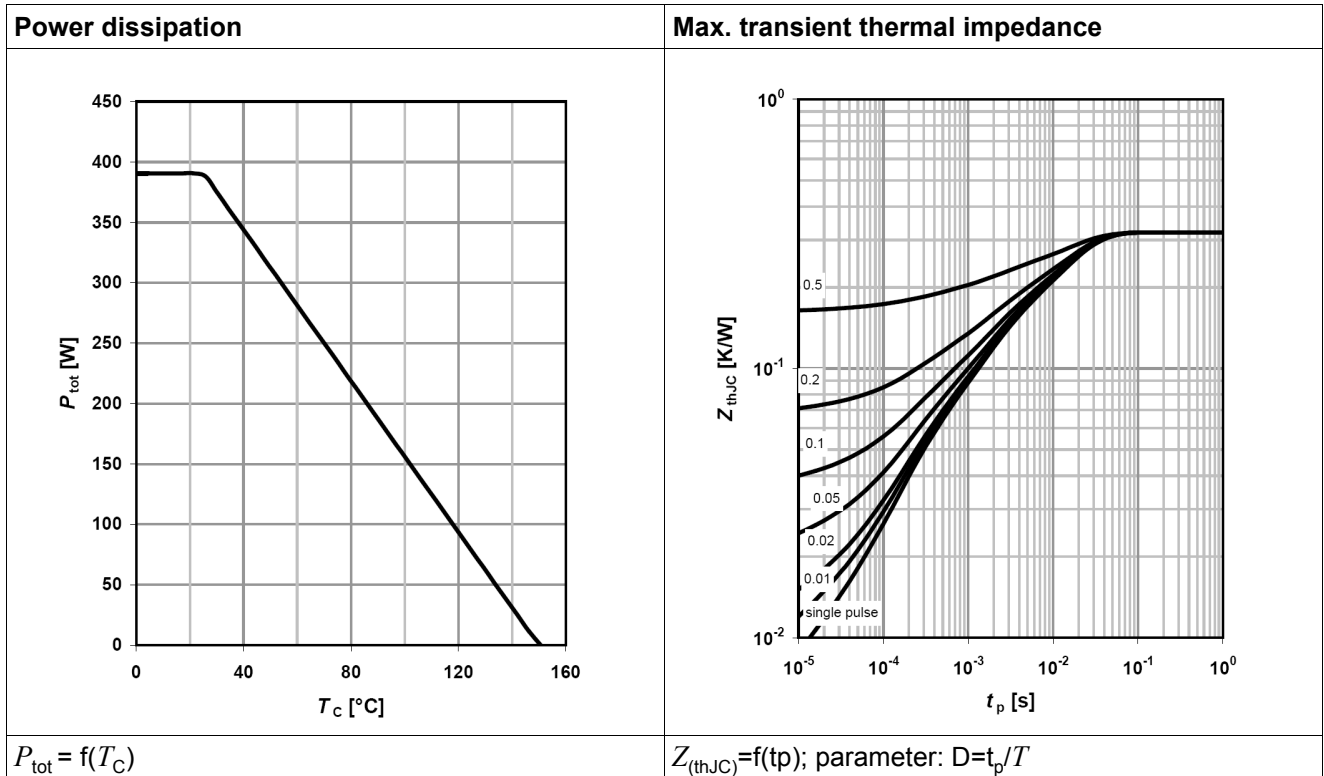
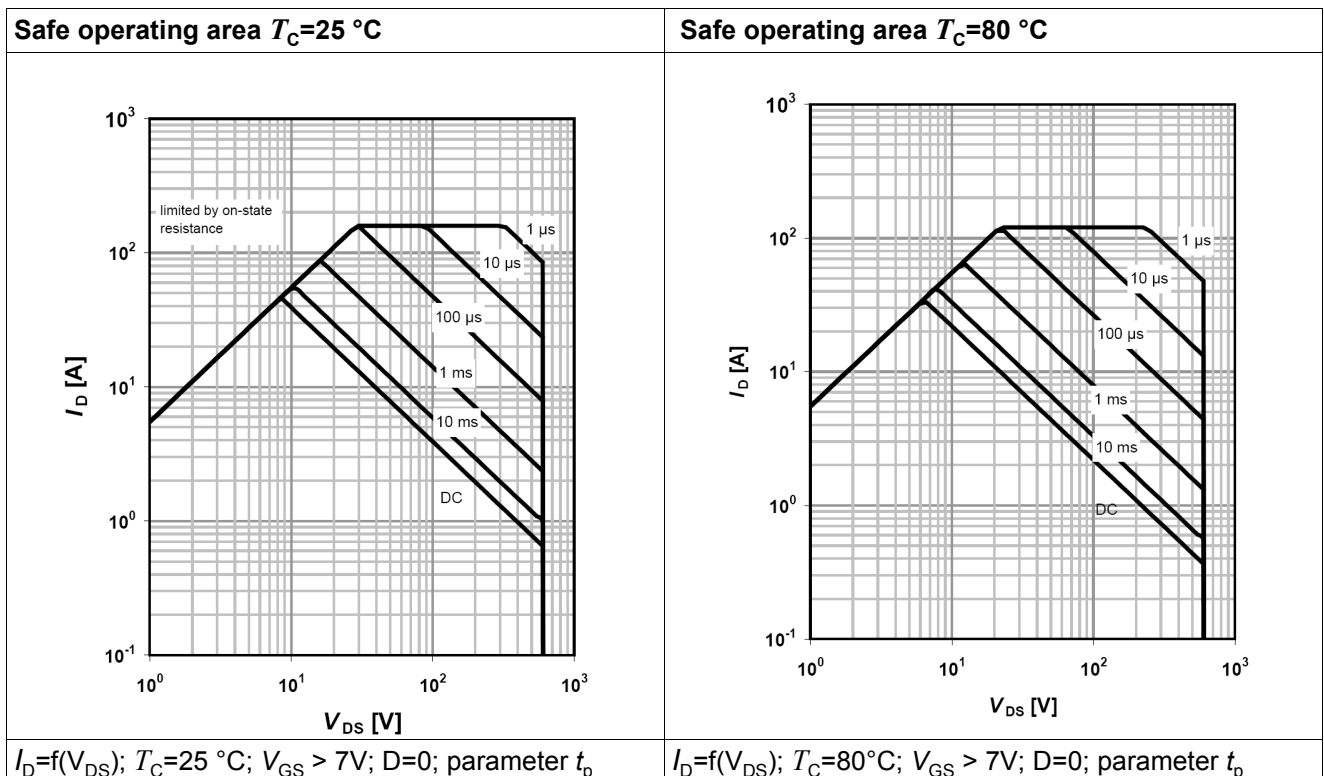


Table 9



Electrical characteristics diagrams

Table 10

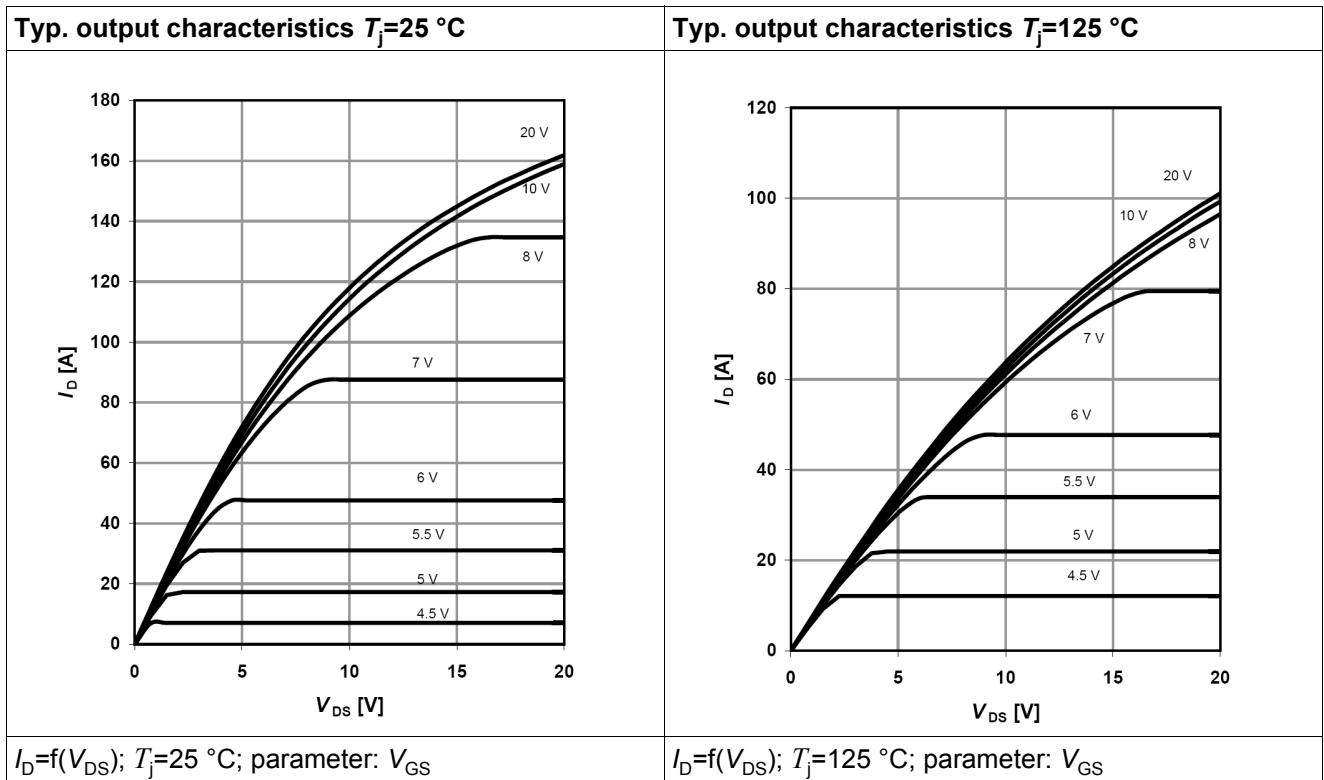


Table 11

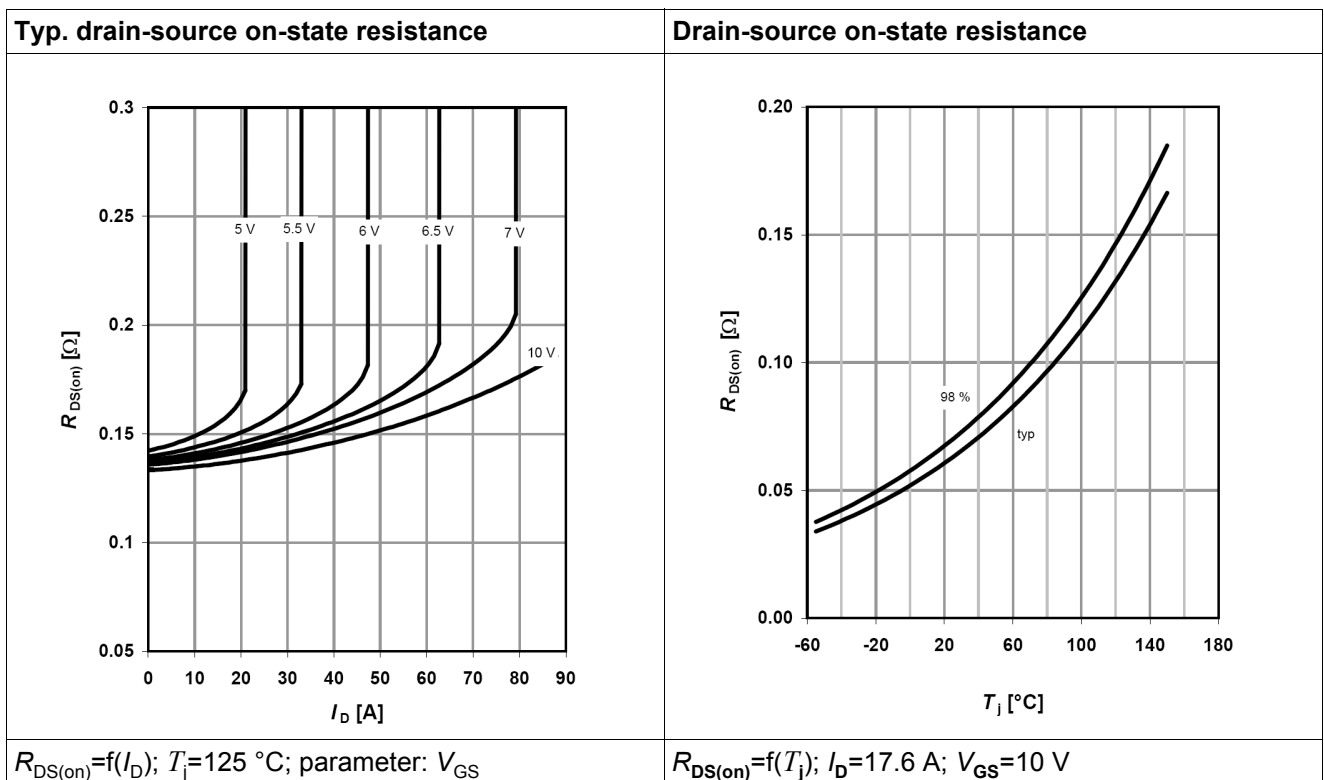




Table 12

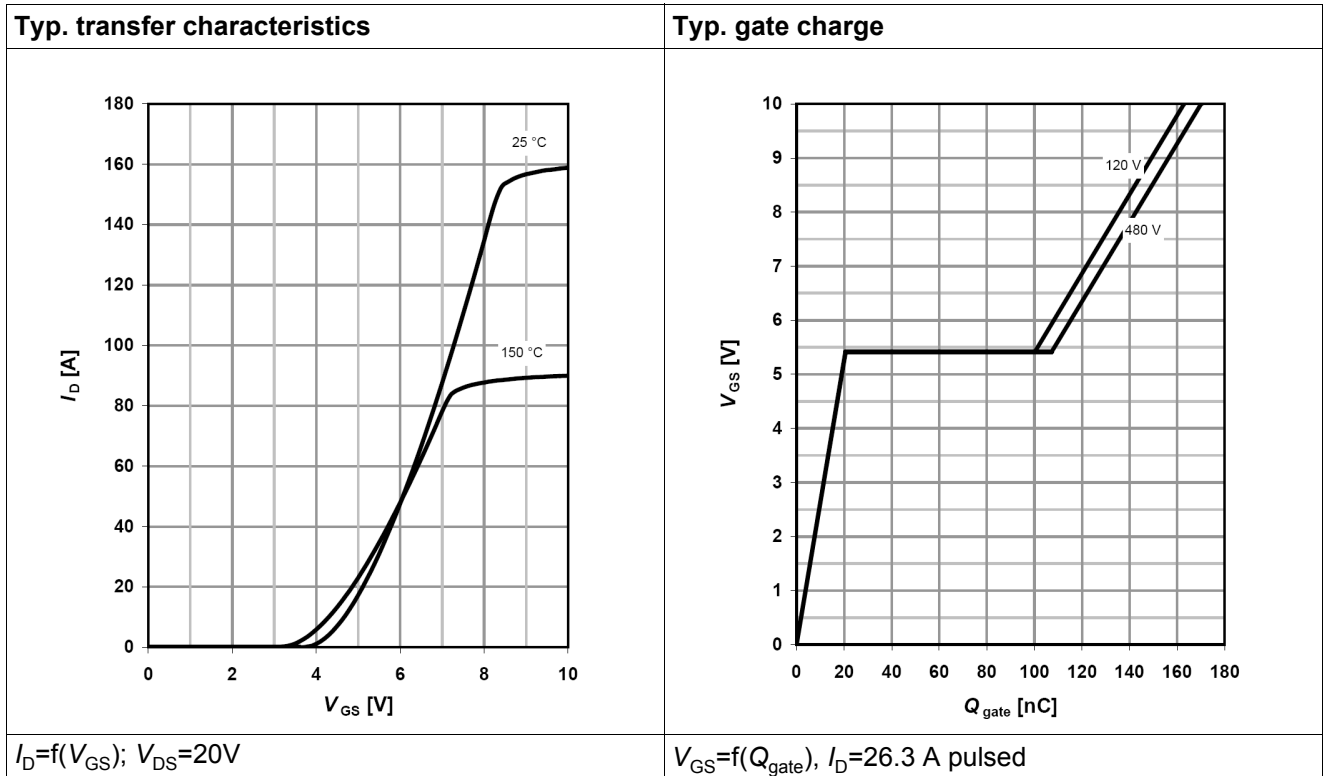


Table 13

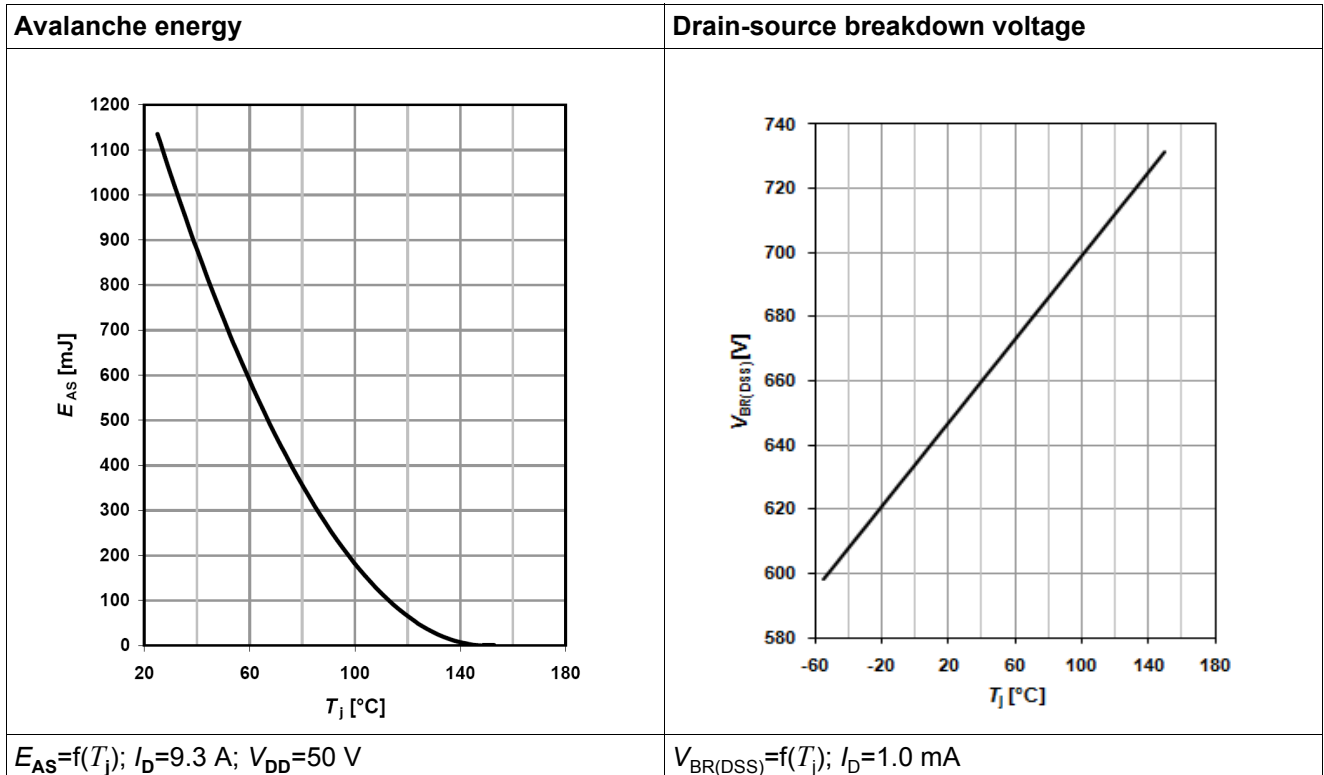


Table 14

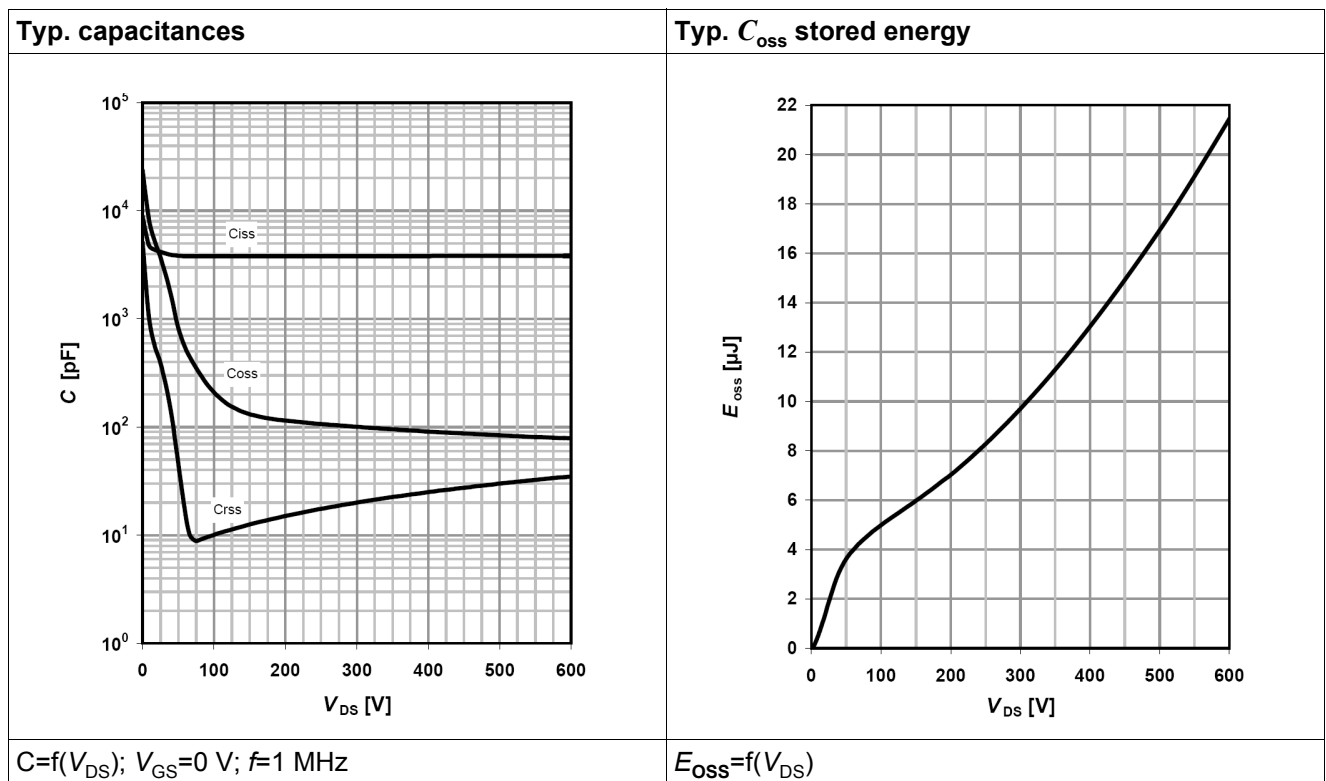
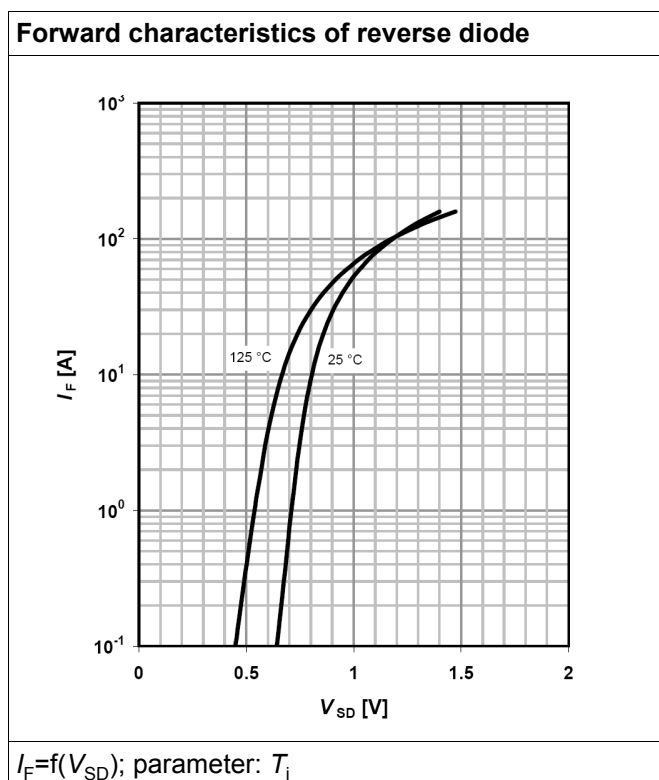


Table 15



6 Package outlines

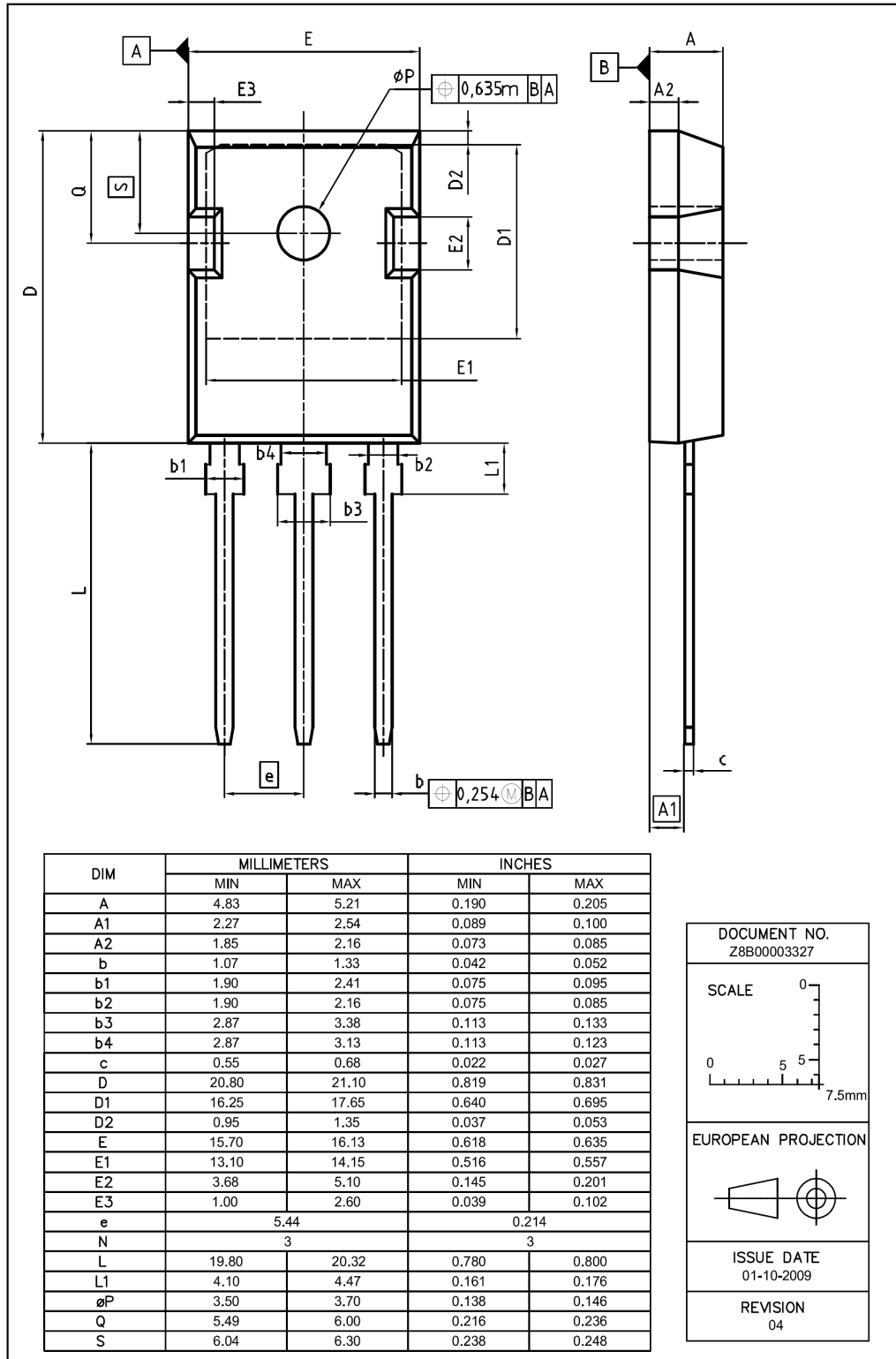


Figure 1 Outlines TO-247, dimensions in mm/inches

## 7 Revision History

Revision History: 2011-03-15, Rev. 2.0

Previous Revision:

Revision	Subjects (major changes since last revision)
2.0	Release of final data sheet

### We Listen to Your Comments

Any information within this document that you feel is wrong, unclear or missing at all?

Your feedback will help us to continuously improve the quality of this document.

Please send your proposal (including a reference to this document) to: [erratum@infineon.com](mailto:erratum@infineon.com)



Edition 2011-03-15

Published by

Infineon Technologies AG

81726 Munich, Germany

© 2011 Infineon Technologies AG

All Rights Reserved.

### Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

### Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest Infineon Technologies Office ([www.infineon.com](http://www.infineon.com)).

### Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.